



PRELIMINARY

SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

SFTX3501-3X-16Q

**TRIPLE UNCOMMITTED
300mA
150 Volt
NPN TRANSISTOR**

Designer's Data Sheet

FEATURES:

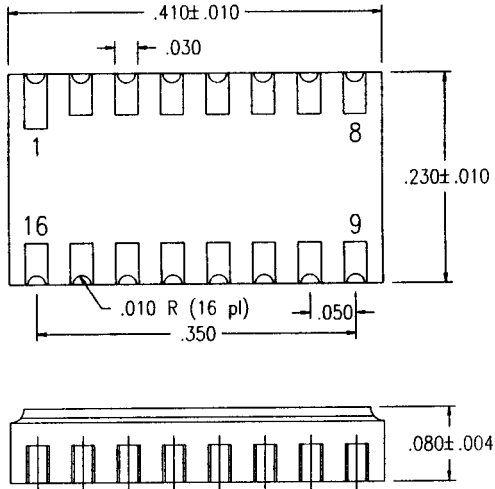
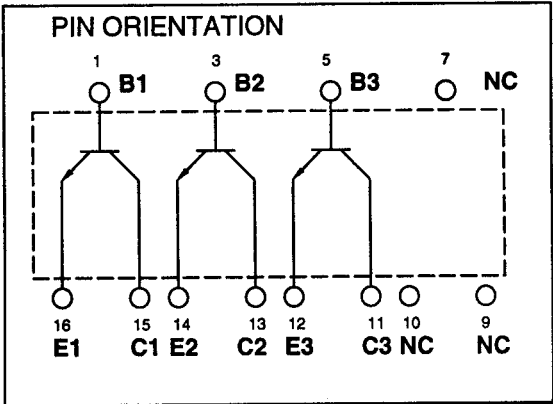
- Eutectic Die Attach, Hermetic Package
- Electrical performance similar to 3 X 2N3501 in one package

16 PIN QUAD CLCC

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Collector-Emitter Voltage	V _{CEO}	150	V
Collector-Base Voltage	V _{CBO}	150	V
Emitter-Base Voltage	V _{EB0}	6.0	V
Collector Current (per transistor)	I _C	300	mA
Total Device Dissipation @ TC= 25°C (All three transistors)	P _D	7.0	W
Operating and Storage Temperature	T _J , T _{stj}	-55 to +200	°C
Thermal Resistance, Junction to Case (all 3 transistors)	R _{θJC}	25	°C/W

PACKAGE OUTLINE: 16 PIN QUAD CLCC



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: XN0023 D

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SFTX3501-3X-16Q**SOLID STATE DEVICES, INC**14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424**ELECTRICAL CHARACTERISTICS (Per Transistor) @ TA=25°C (Unless Otherwise Specified)**

RATING	SYMBOL	MIN	MAX	UNIT	
Collector-Emitter Breakdown Voltage (IC= 10.0mAdc, IB=0 A)	BVCEO	150	---	V	
Collector- Base Breakdown Voltage (IC= 10.0μAdc, IE=0 A)	BVCBO	150	---	V	
Emitter-Base Breakdown Voltage (IE = 10μAdc, IC=0 A)	BVEBO	6	---	V	
Collector-Base Cutoff Current (VCB= 75 Vdc, IE=0 A) (VCB=75 Vdc, IE=0A, TA=150°C)	ICBO	---	50 50	nA uA	
Emitter Cutoff Current (VEB = 4 Vdc)	IEBO	---	25	nA	
DC Current Gain (IC= 0.1 mAdc, VCE= 10 Vdc) (IC= 150 mAdc, VCE= 10 Vdc) (IC=150mAdc, VCE=10Vdc, TA=150°C)	HFE	35 100 45	---	---	
Collector -Emitter Saturation Voltage (IC= 150 mAdc, IB = 15 mAdc)	VCE(SAT)	---	0.4	V	
Base-Emitter Saturation Voltage (IC= 150 mAdc, IB = 15 mAdc)	VBE(SAT)	---	1.2	V	
Output Capacitance (VCB= 10 Vdc, IE= 0 Adc, f=1MHz)	Cob	---	10	pF	
Input Capacitance (VBE= 0.5 Vdc, IC= 0 Adc, f=1MHz)	Cib	---	80	pF	
On Time	IC= 150 mAdc Vcc=100Vdc IB1=15 mAdc VEB=-2 Vdc	ton	---	115	nsec
Off Time	IC=150mA Vcc=100Vdc IB1= -IB2=15 mAdc	toff	---	1150	

For thermal derating curves and other characteristic curves please contact SSDI Marketing Department.